



IRL510STRL Information



For Reference Only

Part Number IRL510STRL **Manufacturer** Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single MOSFET N-CH 100V 5.6A D2PAK

Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Description









IRL510STRL Specifications

Manufacturer Part Number IRL510STRL Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 5.6A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4V, 5V Vgs(th) (Max) @ Id 2V @ 250µA Gate Charge (Qg) (Max) @ Vgs 6.In C @ 5V Input Capacitance (Ciss) (Max) @ Vds 250pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 3.7W (Ta), 43W (Tc) Rds On (Max) @ Id, Vgs 540 mOhm @ 3.4A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Report errors?		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C5.6A (Tc)Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs6.1nC @ 5VInput Capacitance (Ciss) (Max) @ Vds250pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)3.7W (Ta), 43W (Tc)Rds On (Max) @ Id, Vgs540 mOhm @ 3.4A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C5.6A (Tc)Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs6.1nC @ 5VInput Capacitance (Ciss) (Max) @ Vds250pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)3.7W (Ta), 43W (Tc)Rds On (Max) @ Id, Vgs540 mOhm @ 3.4A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Series	-
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Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Journal of Temperature Surplier Device Package Package / Case 5.6A (Tc) 6.1B (Subject of the state of	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4V, 5VVgs(th) (Max) @ Id2V @ 250μAGate Charge (Qg) (Max) @ Vgs6.1nC @ 5VInput Capacitance (Ciss) (Max) @ Vds250pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)3.7W (Ta), 43W (Tc)Rds On (Max) @ Id, Vgs540 mOhm @ 3.4A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 2V @ 250μA 6.1nC @ 5V 250pF @ 25V 25	Current - Continuous Drain (Id) @ 25°C	5.6A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 250pF @ 25V Vgs (Max) ±10V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 540 mOhm @ 3.4A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drive Voltage (Max Rds On, Min Rds On)	4V, 5V
Input Capacitance (Ciss) (Max) @ Vds 250pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 540 mOhm @ 3.4A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs(th) (Max) @ Id	2V @ 250μA
Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 3.7W (Ta), 43W (Tc) Rds On (Max) @ Id, Vgs 540 mOhm @ 3.4A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Gate Charge (Qg) (Max) @ Vgs	6.1nC @ 5V
FET Feature - Power Dissipation (Max) 3.7W (Ta), 43W (Tc) Rds On (Max) @ Id, Vgs 540 mOhm @ 3.4A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Input Capacitance (Ciss) (Max) @ Vds	250pF @ 25V
Power Dissipation (Max) 3.7W (Ta), 43W (Tc) 8ds On (Max) @ Id, Vgs 540 mOhm @ 3.4A, 5V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs (Max)	±10V
Rds On (Max) @ Id, Vgs540 mOhm @ 3.4A, 5VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Power Dissipation (Max)	3.7W (Ta), 43W (Tc)
Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Rds On (Max) @ Id, Vgs	540 mOhm @ 3.4A, 5V
Supplier Device Package D2PAK Package / Case D2PAK TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Mounting Type	Surface Mount
	Supplier Device Package	D2PAK
Report errors?	Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
		Report errors?

IRL510STRL Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRL510STRL Payment Methods



















IRL510STRL Shipping Methods













If you have any question about IRL510STRL, please do not hesitate to contact us!

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